S	CHD8-06 URFACE MOUNT SILICON HYPERFAST		ctor Corp.	vw.centralsemi.com	
POWER RECTIFIER 8.0 AMP, 600 VOLT		The CENTRAL SEMICONDUCTOR CHD8-06 is a high voltage silicon HyperFast power rectifier designed for extremely fast switching applications.			
		MARKING: FULL PART NUMBER			
DPAK CASE FEATURES: • High current capability					
APPLICATIONS:		High surge capacity			
Power factor correction		HyperFast recovery time (22ns TYP)			
Motor control		• High voltage			
ΜΑΧΙΜυΙ	II RATINGS: (T _A =25°C unless otherwise	noted)			
		SYMBOL	000	UNITS	
Peak Repetitive Reverse Voltage		VRRM	600	V	
DC Blocking Voltage		V _R V _{R(RMS)}	600	V	
	RMS Reverse Voltage		420	V	
	Ŭ		0.0	•	
Average F	Forward Current (T _L =100°C)	I _O	8.0	A	
Average F Peak Forv	Forward Current (T _L =100°C) ward Surge Current, tp=8.3ms	IFSM	70	А	
Average F Peak Forv Operating	Forward Current (T _L =100°C) ward Surge Current, tp=8.3ms and Storage Junction Temperature	I _{FSM} T _{J,} T _{stg}	70 -65 to +175	A °C	
Average F Peak Forv Operating	Forward Current (T _L =100°C) ward Surge Current, tp=8.3ms	IFSM	70	А	
Average F Peak Forv Operating Thermal F ELECTRI	Forward Current (T _L =100°C) ward Surge Current, tp=8.3ms and Storage Junction Temperature Resistance CAL CHARACTERISTICS: (T _A =25°C un	^I FSM T _J , T _{stg} Θ _{JL} less otherwise no	70 -65 to +175 5.0	A °C °C/W	
Average F Peak Forv Operating Thermal F ELECTRI SYMBOL	Forward Current (T _L =100°C) ward Surge Current, tp=8.3ms and Storage Junction Temperature Resistance CAL CHARACTERISTICS: (T _A =25°C un TEST CONDITIONS	IFSM T _{J,} T _{stg} ^Θ JL	70 -65 to +175 5.0 max	A ℃ ℃/W UNITS	
Average F Peak Forv Operating Thermal F ELECTRI SYMBOL	Forward Current (T _L =100°C) ward Surge Current, tp=8.3ms and Storage Junction Temperature Resistance CAL CHARACTERISTICS: (T _A =25°C un TEST CONDITIONS V _R =600V	^I FSM T _J , T _{stg} Θ _{JL} less otherwise no	70 -65 to +175 5.0 oted) MAX 10	Α °C °C/W UNITS μΑ	
Average F Peak Forv Operating Thermal F ELECTRI SYMBOL ^I R ^I R	Forward Current (T_L =100°C) ward Surge Current, tp=8.3ms and Storage Junction Temperature Resistance CAL CHARACTERISTICS: (T_A =25°C un TEST CONDITIONS V _R =600V V _R =600V, T_A =150°C	IFSM T _J , T _{stg} Θ _{JL} less otherwise no TYP	70 -65 to +175 5.0 max	A ℃ ℃/W UNITS	
Average F Peak Forv Operating Thermal F ELECTRI SYMBOL	Forward Current (T _L =100°C) ward Surge Current, tp=8.3ms and Storage Junction Temperature Resistance CAL CHARACTERISTICS: (T _A =25°C un TEST CONDITIONS V _R =600V	^I FSM T _J , T _{stg} Θ _{JL} less otherwise no	70 -65 to +175 5.0 oted) MAX 10 500	Α °C °C/W UNITS μΑ μΑ	

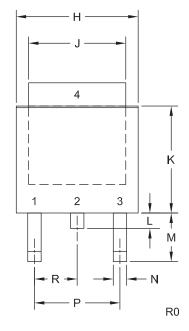
R3 (31-August 2016)





SURFACE MOUNT SILICON HYPERFAST **POWER RECTIFIER** 8.0 AMP, 600 VOLT

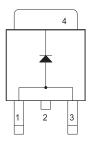
Α -В С 1 D Ε 1 F G



LEAD CODE:

- 1) Anode
- 2) Cathode 3) Anode
- 4) Cathode
- Pin 2 is common to the tab (4)

MARKING: FULL PART NUMBER



DIMENSIONS									
	INCHES		MILLIMETERS						
SYMBOL	MIN	MAX	MIN	MAX					
А	0.083	0.108	2.10	2.75					
В	0.016	0.032	0.40	0.81					
С	0.035	0.063	0.89	1.60					
D	0.203	0.228	5.15	5.79					
E	0.020	-	0.51	-					
F	0.018	0.024	0.45	0.60					
G	0.051	0.071	1.30	1.80					
Н	0.248	0.268	6.30	6.81					
J	0.197	0.217	5.00	5.50					
K	0.209	0.245	5.30	6.22					
L	0.025	0.040	0.64	1.02					
М	0.090	0.115	2.30	2.91					
N	0.012	0.045	0.30	1.14					
Р	0.180		4.60						
R	0.090		2.30						
DPAK (REV: R0)									

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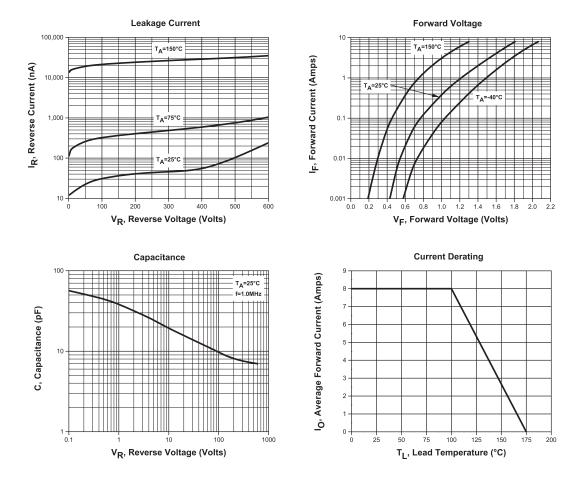
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DPAK CASE - MECHANICAL OUTLINE



SURFACE MOUNT SILICON HYPERFAST POWER RECTIFIER 8.0 AMP, 600 VOLT





TYPICAL ELECTRICAL CHARACTERISTICS

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OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- · Consolidated shipping options

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities

ss your design challenges.

· Custom product packing

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits

Custom bar coding for shipments

Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

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